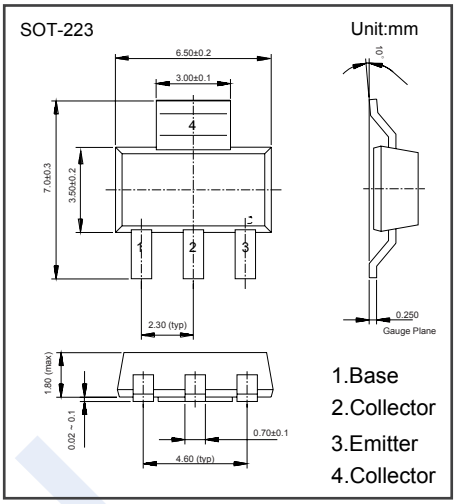
PNP Transistors

FZT549 (KZT549)



■ Features

- Collector Current Capability I_C=-1A
- Collector Emitter Voltage V_{CEO}=-30V

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-35	V
Collector - Emitter Voltage	V_{CEO}	-30	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-1	A
Collector Current - Pulse	I_{CP}	-2	
Collector Power Dissipation	P_C	2	W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-35			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, I_B=0	-30			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -30 V , I_E=0			-0.1	uA
		V_{CB}= -30 V , I_E=0 ,Ta = 100℃			-10	
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1 A, I_B=-100mA (Note.1)			-0.5	V
		I_C=-2 A, I_B=-200mA (Note.1)			-0.75	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-1 A, I_B=-100mA (Note.1)			-1.25	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	V_{CE}= -2V, I_C= -1A (Note.1)			-1	
DC current gain (Note.1)	$h_{FE(1)}$	V_{CE}= -2V, I_C= -50mA	70			
	$h_{FE(2)}$	V_{CE}= -2V, I_C= -500mA	100		300	
	$h_{FE(3)}$	V_{CE}= -2V, I_C= -1 A	80			
	$h_{FE(4)}$	V_{CE}= -2V, I_C= -2 A	30			
Collector output capacitance	C_{ob}	V_{CB}= -10V, f=10MHz			10	pF
Transition frequency	f_T	V_{CE}= -5V, I_C= -100mA,f=100MHz	100			MHz

Note.1: Pulse width=300us. Duty cycle ≤ 2%